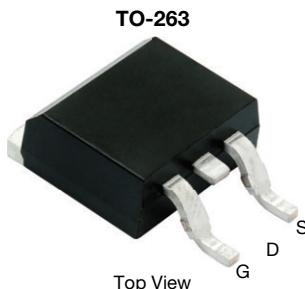


## N-Channel 200 V (D-S) MOSFET



PRODUCT SUMMARY	
$V_{DS}$ (V)	200
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10$ V	0.0114
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 7.5$ V	0.0129
$Q_g$ typ. (nC)	56.7
$I_D$ (A)	150 <sup>d</sup>
Configuration	Single

### FEATURES

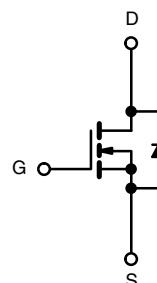
- TrenchFET® power MOSFET
- Maximum 175 °C junction temperature
- Very low  $Q_{gd}$  reduces power loss from passing through  $V_{plateau}$
- 100 %  $R_g$  and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



RoHS  
COMPLIANT  
HALOGEN  
FREE

### APPLICATIONS

- Switching power supply
- DC/DC converter
- Power tools
- Motor drive switch
- DC/AC inverter
- Battery management
- OR-ing / e-fuse



N-Channel MOSFET

### ORDERING INFORMATION

Package	TO-263
Lead (Pb)-free and halogen-free	SUM90100E-GE3

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	200	V
Gate-source voltage	$V_{GS}$	$\pm 20$	
Continuous drain current ( $T_J = 150$ °C)	$I_D$	150 <sup>d</sup>	A
		150 <sup>d</sup>	
Pulsed drain current ( $t = 100$ $\mu$ s)	$I_{DM}$	250	
Avalanche current	$I_{AS}$	70	
Single avalanche energy <sup>a</sup>	$E_{AS}$	245	mJ
Maximum power dissipation <sup>a</sup>	$P_D$	375 <sup>b</sup>	W
		125 <sup>b</sup>	
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +175	°C

### THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient (PCB mount) <sup>c</sup>	$R_{thJA}$	40	°C/W
Junction-to-case (drain)	$R_{thJC}$	0.4	

#### Notes

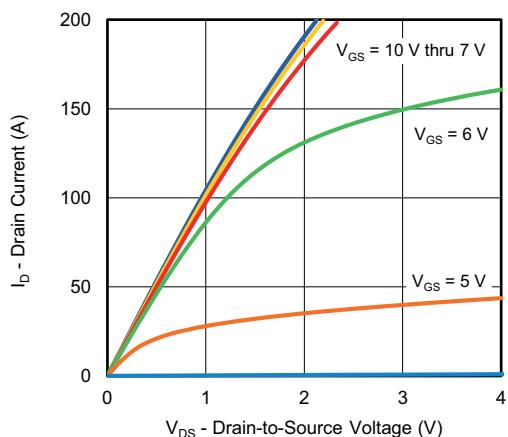
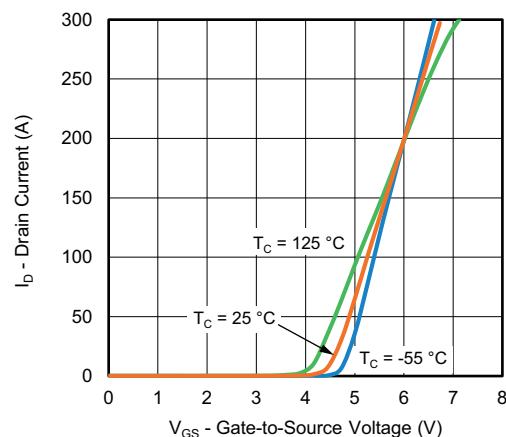
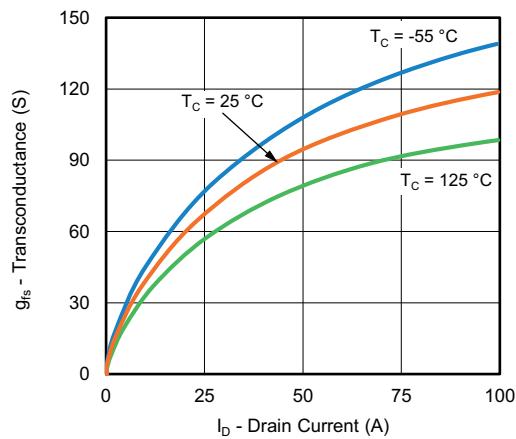
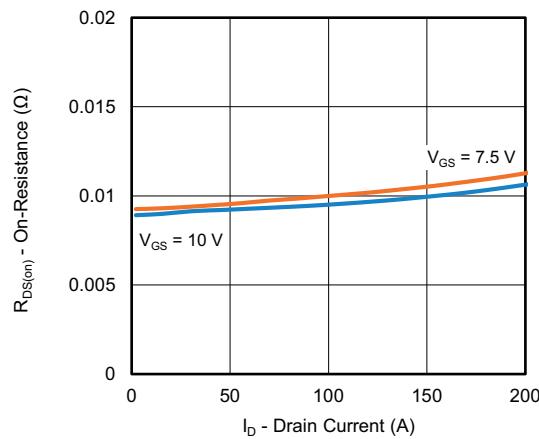
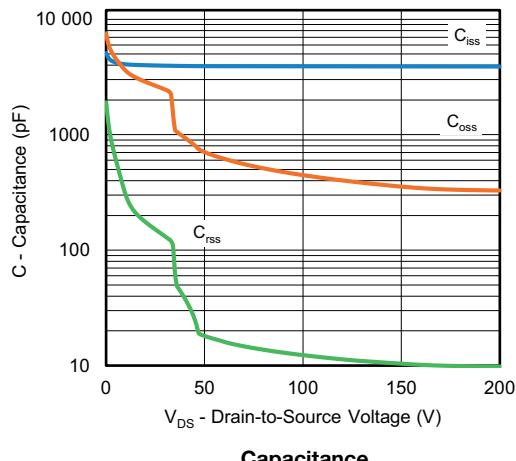
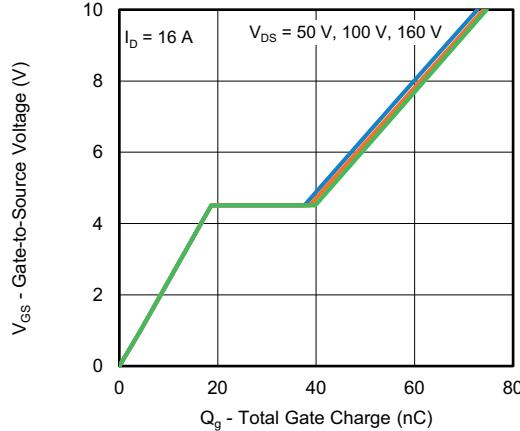
- Duty cycle  $\leq 1$  %
- See SOA curve for voltage derating
- When mounted on 1" square PCB (FR4 material)
- Package limited

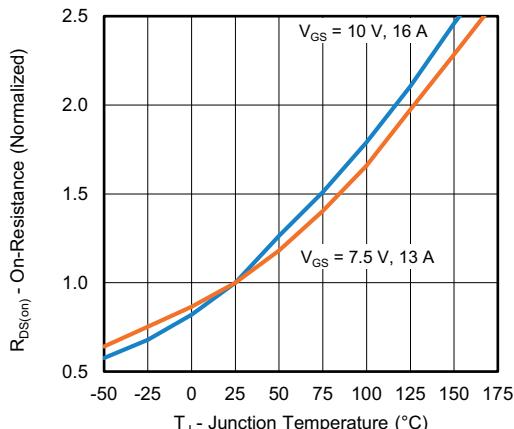
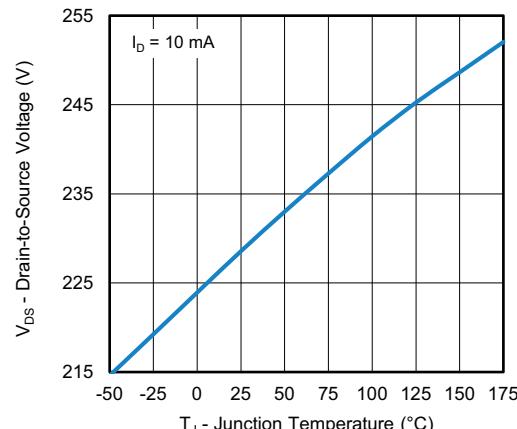
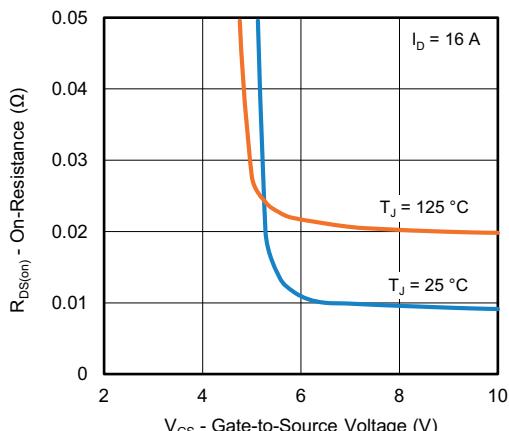
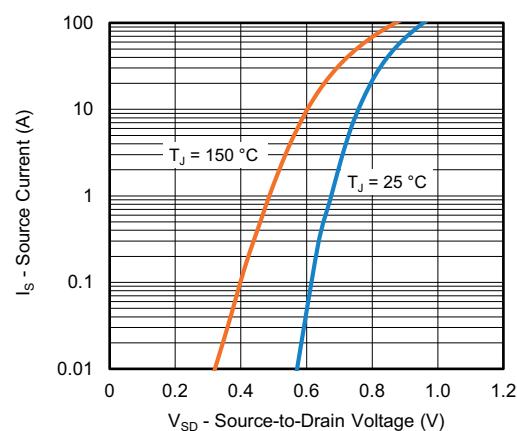
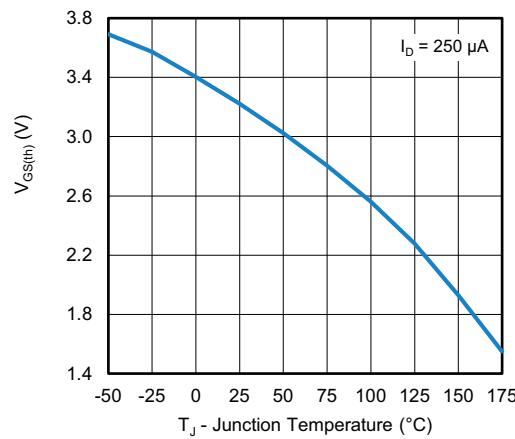
<b>SPECIFICATIONS</b> ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	200	-	-	V
Gate threshold voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2	-	4	
Gate-body leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$	-	-	$\pm 250$	$\text{nA}$
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 200\text{ V}$ , $V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 200\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125^\circ\text{C}$	-	-	150	
		$V_{DS} = 200\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 175^\circ\text{C}$	-	-	5	
On-state drain current <sup>a</sup>	$I_{D(\text{on})}$	$V_{DS} \geq 10\text{ V}$ , $V_{GS} = 10\text{ V}$	120	-	-	A
Drain-source on-state resistance <sup>a</sup>	$R_{DS(\text{on})}$	$V_{GS} = 10\text{ V}$ , $I_D = 16\text{ A}$	-	0.0095	0.0114	$\Omega$
		$V_{GS} = 7.5\text{ V}$ , $I_D = 13\text{ A}$	-	0.0099	0.0129	
Forward transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}$ , $I_D = 13\text{ A}$	-	85	-	S
<b>Dynamic</b> <sup>b</sup>						
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$	-	3930	-	$\text{pF}$
Output capacitance	$C_{oss}$		-	450	-	
Reverse transfer capacitance	$C_{rss}$		-	12	-	
Total gate charge <sup>c</sup>	$Q_g$	$V_{DS} = 100\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 16\text{ A}$	-	72.8	110	$\text{nC}$
Gate-source charge <sup>c</sup>	$Q_{gs}$		-	19.4	-	
Gate-drain charge <sup>c</sup>	$Q_{gd}$		-	19.0	-	
Gate resistance	$R_g$	$f = 1\text{ MHz}$	0.7	3.5	7.0	$\Omega$
Turn-on delay time <sup>c</sup>	$t_{d(\text{on})}$	$V_{DD} = 80\text{ V}$ , $R_L = 6.2\text{ }\Omega$ $I_D \approx 13\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\text{ }\Omega$	-	20	40	$\text{ns}$
Rise time <sup>c</sup>	$t_r$		-	50	100	
Turn-off delay time <sup>c</sup>	$t_{d(\text{off})}$		-	60	120	
Fall time <sup>c</sup>	$t_f$		-	18	36	
<b>Drain-Source Body Diode Ratings and Characteristics</b> <sup>b</sup> ( $T_C = 25^\circ\text{C}$ )						
Pulsed current ( $t = 100\text{ }\mu\text{s}$ )	$I_{SM}$	$I_F = 10\text{ A}$ , $V_{GS} = 0\text{ V}$ $I_F = 13\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$	-	-	250	A
Forward voltage <sup>a</sup>	$V_{SD}$		-	0.8	1.5	V
Reverse recovery time	$t_{rr}$		-	118	177	ns
Peak reverse recovery charge	$I_{RM(\text{REC})}$		-	9.4	14.1	A
Reverse recovery charge	$Q_{rr}$		-	0.632	0.948	$\mu\text{C}$
Reverse recovery fall time	$t_a$		-	94	-	ns
Reverse recovery rise time	$t_b$		-	24	-	

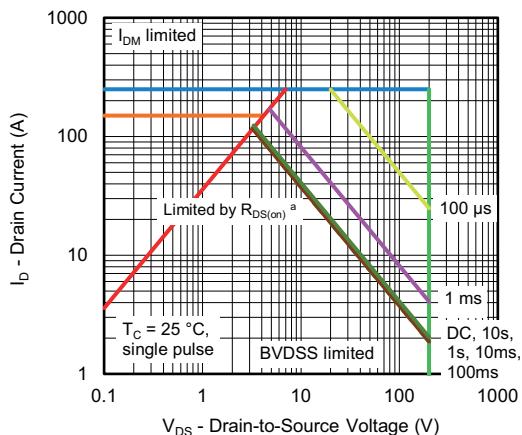
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

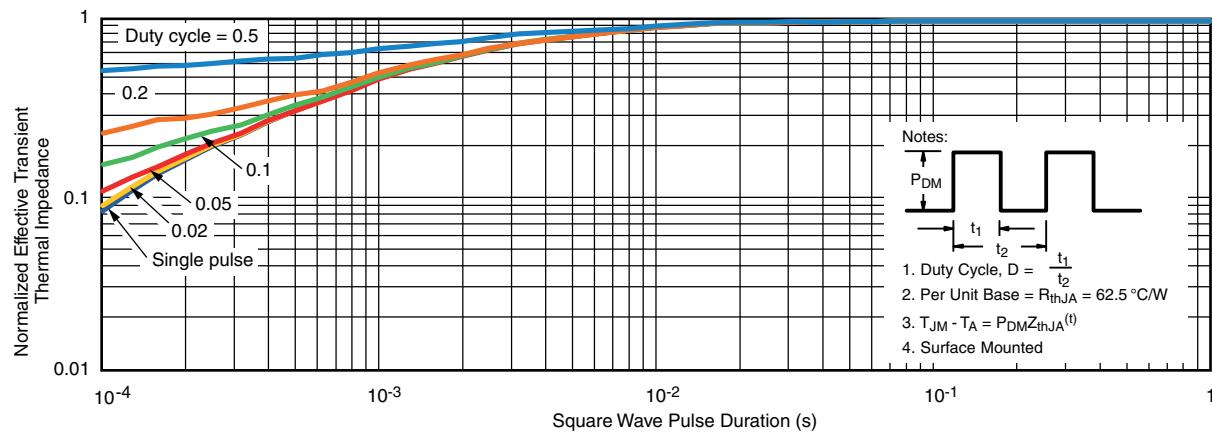
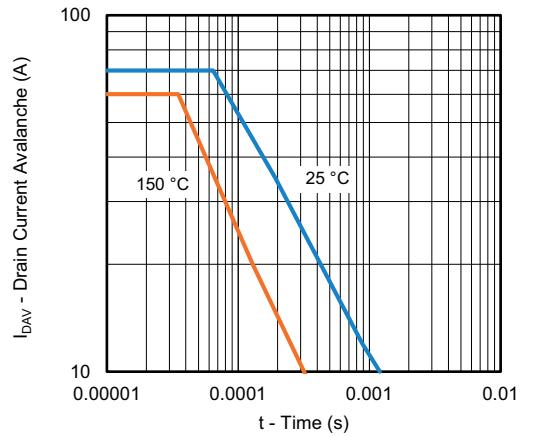
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

**Output Characteristics**

**Transfer Characteristics**

**Transconductance**

**On-Resistance vs. Drain Current**

**Capacitance**

**Gate Charge**

**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

**On-Resistance vs. Junction Temperature**

**Drain Source Breakdown vs. Junction Temperature**

**On-Resistance vs. Gate-to-Source Voltage**

**Source Drain Diode Forward Voltage**

**Threshold Voltage**

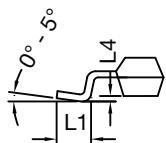
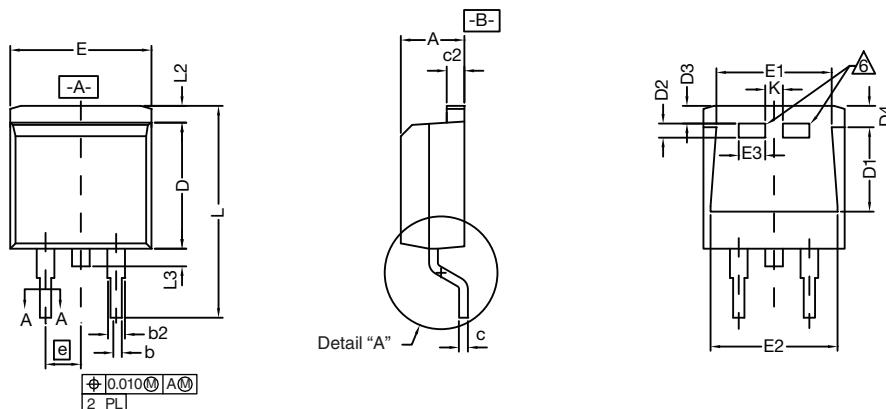
**THERMAL RATINGS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

**Note**

a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

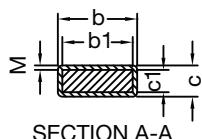


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### TO-263 (D<sup>2</sup>PAK): 3-LEAD



DETAIL A (ROTATED 90°)



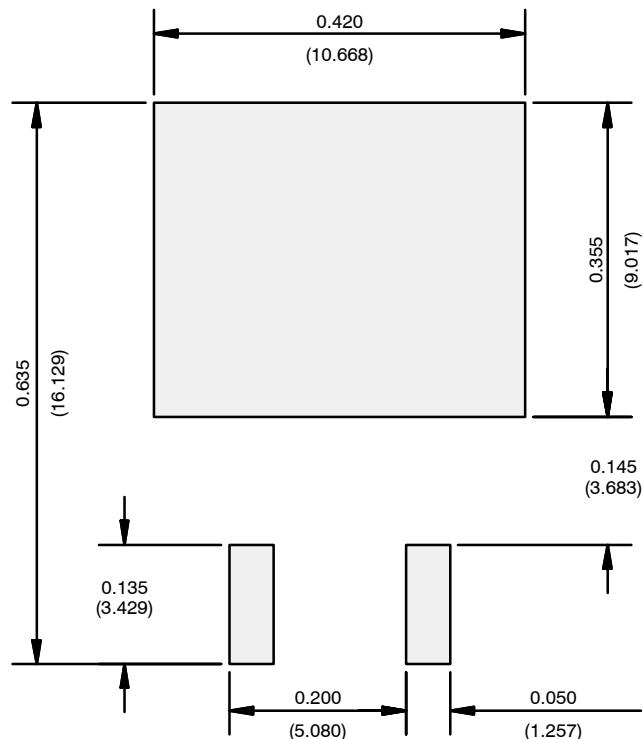
SECTION A-A

#### Notes

1. Plane B includes maximum features of heat sink tab and plastic.
2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
3. Pin-to-pin coplanarity max. 4 mils.
4. \*: Thin lead is for SUB, SYB.  
Thick lead is for SUM, SYM, SQM.
5. Use inches as the primary measurement.

 This feature is for thick lead.

DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
D4	0.044	0.052	1.118	1.321	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.355	0.375	9.017	9.525	
E3	0.072	0.078	1.829	1.981	
e	0.100 BSC		2.54 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
M	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**

Recommended Minimum Pads  
Dimensions in Inches/(mm)

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